

**AMENDMENTS TO THE CLAIMS**

The following is a complete, marked-up listing of revised claims with a status identifier in parenthesis, underlined text indicating insertions, and strike through and/or double-bracketed text indicating deletions.

**LISTING OF CLAIMS**

1.-21. (Cancelled).

22. (Currently Amended) A capacitor of a semiconductor device, the capacitor comprising:

a lower electrode formed on a semiconductor substrate;  
an AHO<sub>y</sub>((Al<sub>x</sub>,Hf<sub>1-x</sub>)O<sub>y</sub>) film formed on the lower electrode;  
an upper electrode formed on the AHO ((Al<sub>x</sub>,Hf<sub>1-x</sub>)O<sub>y</sub>) film; and  
a dielectric film having a dielectric constant that is higher than that of the AHO ((Al<sub>x</sub>,Hf<sub>1-x</sub>)O<sub>y</sub>) film between the upper electrode and the AHO ((Al<sub>x</sub>,Hf<sub>1-x</sub>)O<sub>y</sub>) film,  
wherein the dielectric film is an HfO<sub>2</sub> layer, a ZrO<sub>2</sub> layer, or an STO layer, and  
wherein the dielectric film is directly in contact with the upper electrode.

23. (Currently Amended) The capacitor of claim 22, further comprising:  
an oxidation barrier film formed between the lower electrode and the AHO ((Al<sub>x</sub>,Hf<sub>1-x</sub>)O<sub>y</sub>) film.

24.-37. (Cancelled).

\*\*\* END CLAIM LISTING \*\*\*